

20V PNP MEDIUM POWER TRANSISTOR IN SOT23F

Features

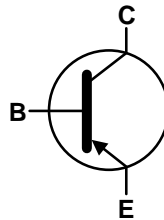
- $BV_{CEO} > -20V$
- $BV_{ECO} > -4V$
- $I_C = -5.5A$ Continuous Collector Current
- $I_{CM} = -15A$ Peak Current
- Guaranteed Gain at I_C of -10A
- $V_{CE(SAT)} < -44mV @ -1A$
- $R_{CE(SAT)} = 26m\Omega$
- 1.5W Power Dissipation
- Complementary PNP Type: ZXTN19020DFF
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Description

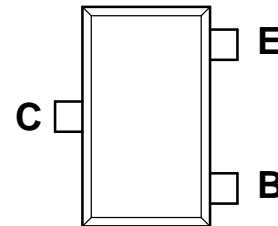
Advanced process capability and package design have been used to maximize the power handling and performance of this small outline transistor. The compact size and ratings of this device make it ideally suited to applications where space is at a premium.



Top View



Device Symbol



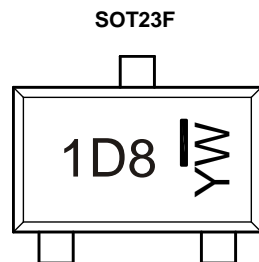
Top View
Pin Configuration

Ordering Information (Note 4)

Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
ZXTP19020DFFTA	AEC-Q101	1D8	7	8	3,000

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



- 1D8 = Product Type Marking Code
 YW = Date Code Marking
 Y = Year: 0~9
 W = Week: A~Z: 1~26
 a~z: 27~52
 z represents 52 & 53 week

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-25	V
Collector-Emitter Voltage (Base Open)	V _{CEO}	-20	V
Emitter – Collector Voltage (Reverse Blocking)	V _{ECO}	-4	V
Emitter-Base Voltage	V _{EBO}	-7	V
Continuous Collector Current	I _C	-5.5	A
Peak Pulse Current	I _{CM}	-15	A
Base Current	I _B	-1	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

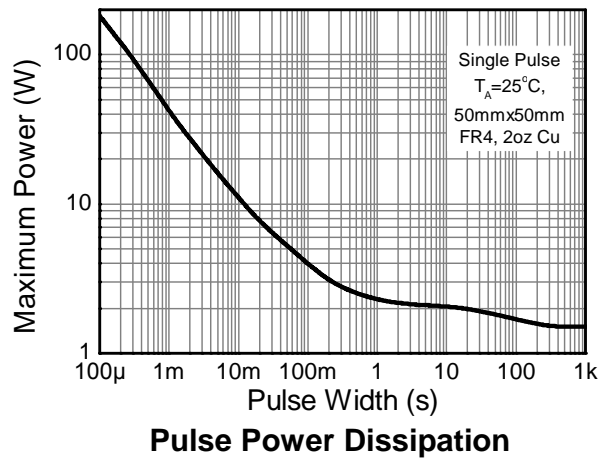
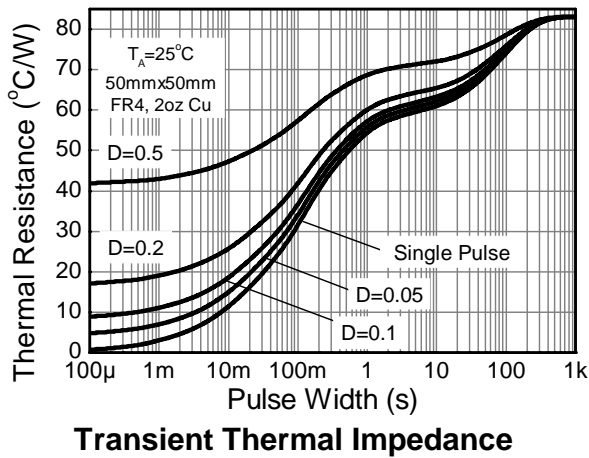
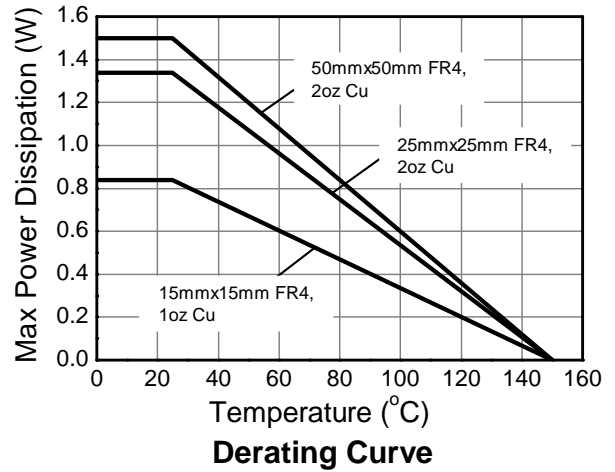
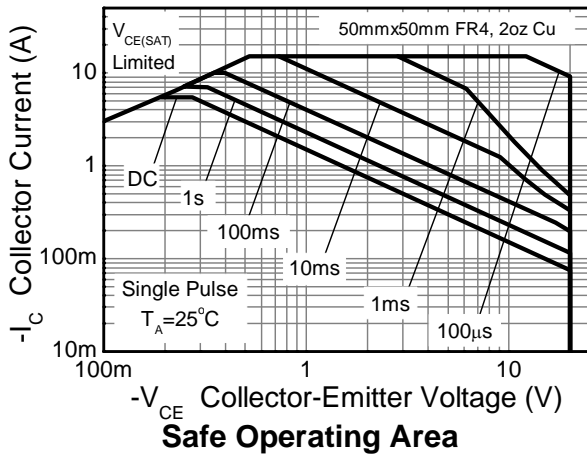
Characteristic	Symbol	Value	Unit	
Power Dissipation Linear Derating Factor	P _D	0.84	W mW/°C	
		(Note 5)		6.72
		(Note 6)		1.34
		(Note 7)		10.72
		(Note 8)		1.50
Thermal Resistance, Junction to Ambient	R _{θJA}	12.0	°C/W	
		(Note 5)		2.0
		(Note 6)		16.0
		(Note 7)		93
Thermal Resistance, Junction to Lead	R _{θJL}	(Note 8)	83	
		(Note 9)	60	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C	

ESD Ratings (Note 10)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge – Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge – Machine Model	ESD MM	400	V	C

- Notes:
- For a device mounted with the exposed collector pad on 15mm x 15mm 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
 - Same as Note 5, except the device is mounted on 25mm x 25mm 2oz copper.
 - Same as Note 5, except the device is mounted on 50mm x 50mm 2oz copper.
 - Same as Note 7, whilst measured at t < 5 seconds.
 - Thermal resistance from junction to solder-point (at the end of the collector lead).
 - Refer to JEDEC specification JESD22-A114 and JESD22-A115.

Thermal Characteristics and Derating Information

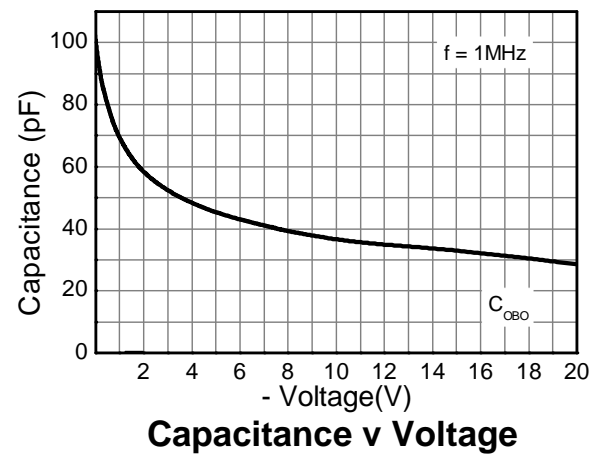
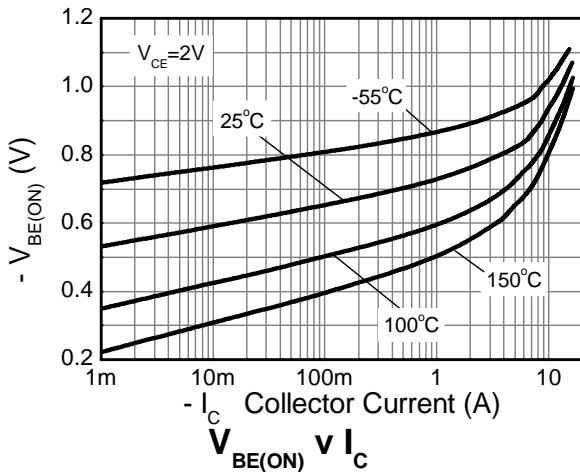
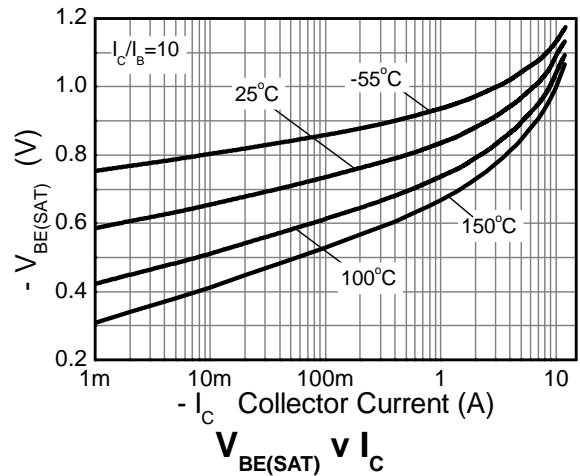
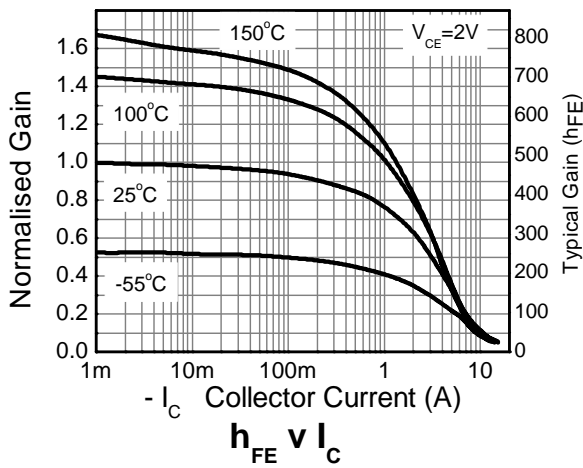
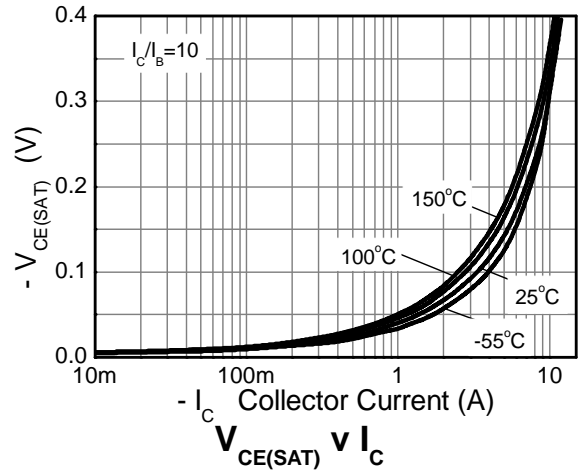
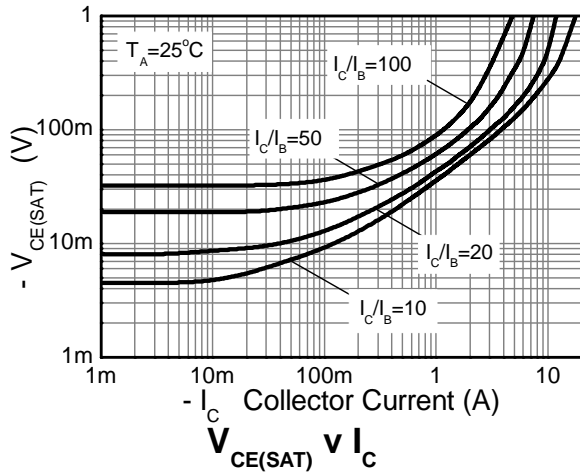


Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV _{CBO}	-25	-55	—	V	I _C = -100μA
Collector-Emitter Breakdown Voltage (Base Open) (Note 11)	BV _{CEO}	-20	-50	—	V	I _C = -10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	-8.6	—	V	I _E = -100μA
Emitter – Collector Breakdown Voltage (Reverse Blocking)	BV _{ECX}	-4	-8.6	—	V	I _E = -100μA, R _{BC} < 1kΩ, or 0.25V > V _{BC} > -0.25V
Emitter – Collector Breakdown Voltage (Base Open)	BV _{ECO}	-4	-8.6	—	V	I _E = -100μA
Collector-Base Cut-off Current	I _{CBO}	—	<-1	-50	nA μA	V _{CB} = -25V V _{CB} = -25V, T _A = +100°C
Emitter-Base Cut-off Current	I _{EBO}	—	<-1	-50	nA	V _{EB} = -5.6V
ON CHARACTERISTICS (Note 11)						
Static Forward Current Transfer Ratio	h _{FE}	300 200 85 25 —	450 310 130 50 20	900 — — — —	—	I _C = -0.1A, V _{CE} = -2V I _C = -2A, V _{CE} = -2V I _C = -5.5A, V _{CE} = -2V I _C = -10A, V _{CE} = -2V I _C = -15A, V _{CE} = -2V
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	—	-37 -90 -105 -160 -145	-44 -125 -140 -210 -175	mV	I _C = -1A, I _B = -100mA I _C = -1A, I _B = -10mA I _C = -2A, I _B = -40mA I _C = -5A, I _B = -250mA I _C = -5.5A, I _B = -550mA
Base-Emitter Saturation Voltage	V _{BE(SAT)}	—	-975	-1050	mV	I _C = -5.5A, I _B = -550mA
Base-Emitter On Voltage	V _{BE(ON)}	—	-830	-900	mV	I _C = -5.5A, V _{CE} = -2V
SMALL SIGNAL CHARACTERISTICS						
Transition Frequency	f _T	—	176	—	MHz	I _C = -50mA, V _{CE} = -10V, f = 50MHz
Input Capacitance	C _{I BO}	—	—	400	pF	V _{EB} = -0.5V, f = 1MHz
Output Capacitance	C _{O BO}	—	36	45	pF	V _{CB} = -10V, f = 1MHz
Delay Time	t _D	—	23	—	ns	V _{CC} = -10V, I _C = -1A, I _{B1} = - I _{B2} = 50mA
Rise Time	t _R	—	18	—	ns	
Storage Time	t _S	—	266	—	ns	
Fall Time	t _F	—	50	—	ns	

Note: 11. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

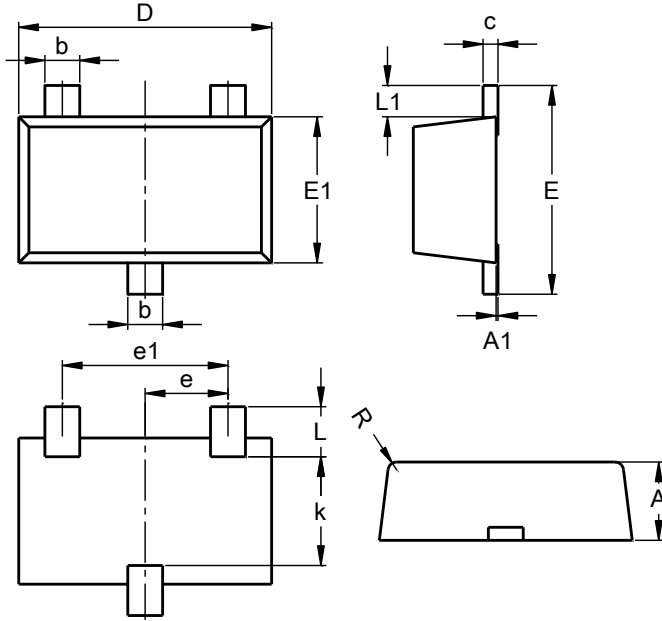
Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)



Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23F

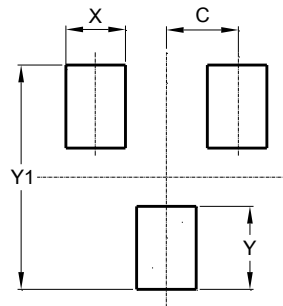


SOT23F			
Dim	Min	Max	Typ
A	0.80	1.00	0.90
A1	0.00	0.10	0.01
b	0.35	0.50	0.44
c	0.10	0.20	0.16
D	2.80	3.00	2.90
e	0.95 REF		
e1	1.90 REF		
E	2.30	2.50	2.40
E1	1.50	1.70	1.65
k	1.20	-	-
L	0.30	0.65	0.50
L1	0.30	0.50	0.40
R	0.05	0.15	-
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23F



Dimensions	Value (in mm)
C	0.95
X	0.80
Y	1.110
Y1	3.000

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